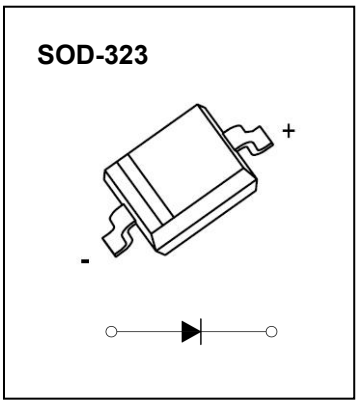
TKSD103AWS-TKSD103CWS

SCHOTTKY BARRIER DIODE

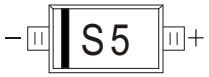
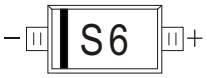
SOD-323 Plastic-Encapsulate Diodes

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Reverse Capacitance



MARKING:

TKSD103AWS:S4	TKSD103BWS:S5	TKSD103CWS:S6
		

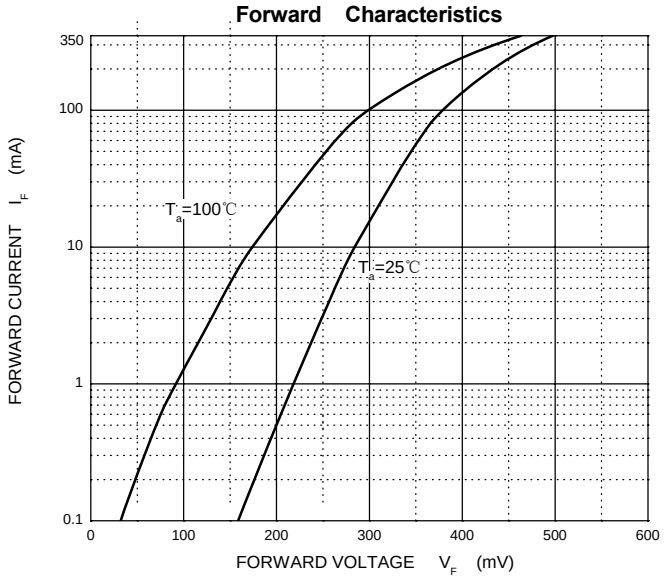
Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25℃

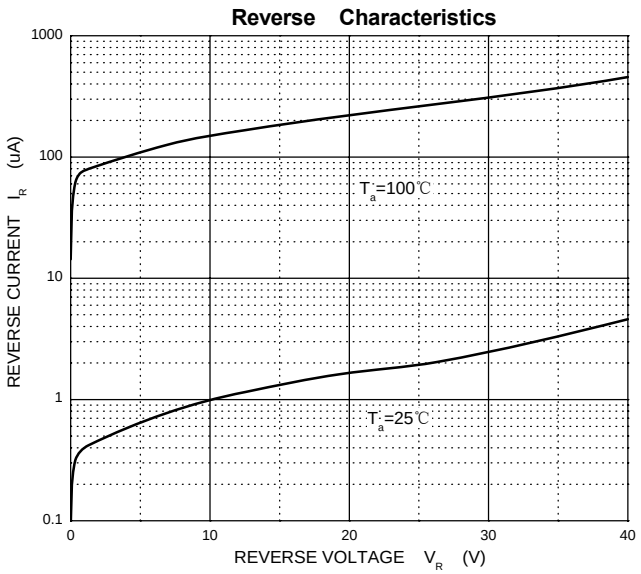
Parameter	Symbol	SD103AWS	SD103BWS	SD103CWS	Unit
Peak Repetitive Peak Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	40	30	20	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	21	14	V
Forward Continuous Current	I_{FM}	350			mA
Non-repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0			A
Power Dissipation	Pd	200			mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	500			℃/W
Junction Temperature	T_j	125			℃
Storage Temperature	T_{STG}	-55~+150			℃

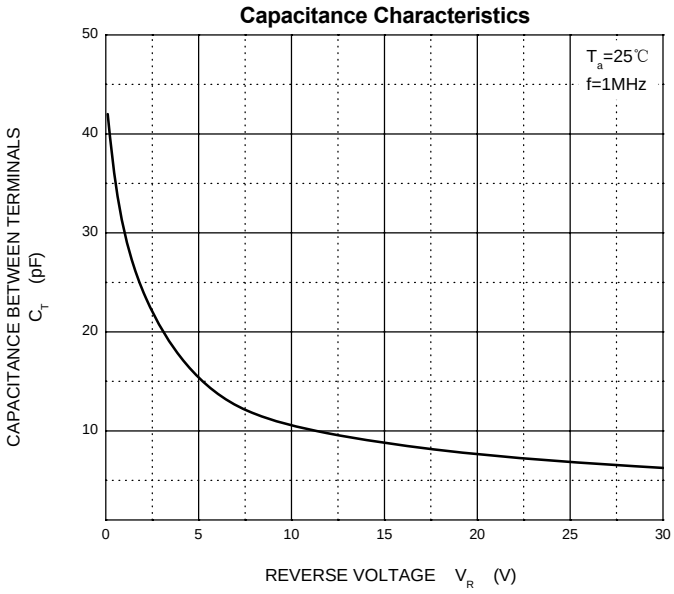
Electrical Ratings @Ta=25℃

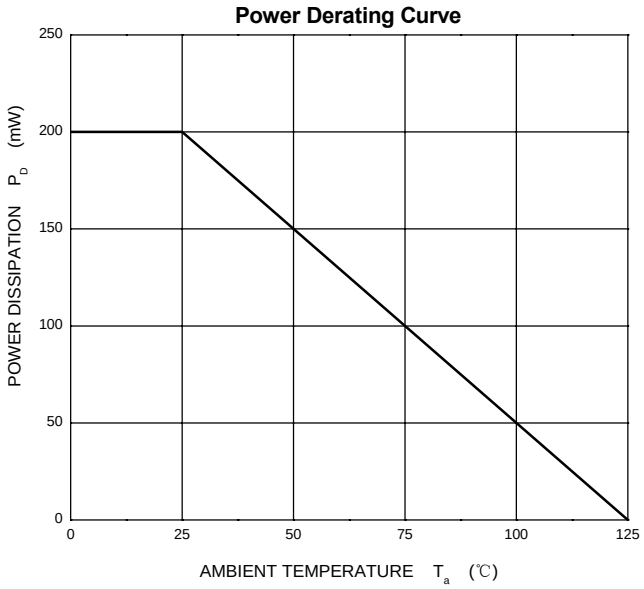
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage TKSD103AWS TKSD103BWS TKSD103CWS	$V_{(BR)}$	 40 30 20			V	 I_R=100μA I_R=100μA I_R=100μA
Forward voltage	V_F			0.37 0.60	V	I_F=20mA I_F=200mA
Reverse current TKSD103AWS TKSD103BWS TKSD103CWS	I_{RM}			5.0	μA	 V_R=30V V_R=20V V_R=10V
Capacitance between terminals	C_T			50	pF	V_R=0V,f=1.0MHz
Reverse recovery time	t_{rr}		10		ns	I_F=I_R=200mA Irr=0.1XI_R,R_L=100Ω

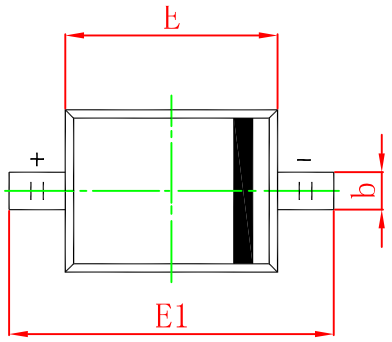
Typical Characteristics

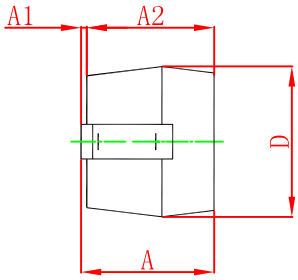


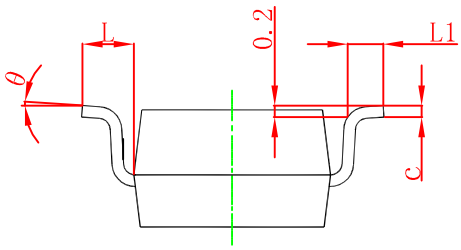






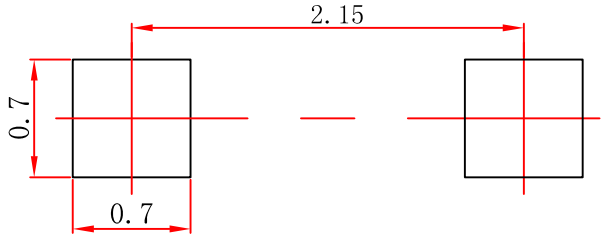






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A		1.000		0.039
A1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.475 REF.		0.019 REF.	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

SOD-323 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.